

Requested Patent: JP11135788A
Title: MANUFACTURE OF SEMICONDUCTOR DEVICE ;
Abstracted Patent: JP11135788 ;
Publication Date: 1999-05-21 ;
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Application Number: JP19970311179 19971027 ;
Priority Number(s): JP19970311179 19971027 ;
IPC Classification: H01L29/78; H01L21/28; H01L21/283; H01L21/336 ;
Equivalents: ;

ABSTRACT:

PROBLEM TO BE SOLVED: To provide a manufacturing method, in which a semiconductor device having an effect preventing a diffused layer from being short-circuited with a silicide film on a gate electrode is formed simply and with good controllability. SOLUTION: A gate electrode 25, provided with normally doped polysilicon films 33 on the upper side and the lower side of a heavily doped polysilicon film 34 in the central layer, is formed on a silicon substrate 21 via a gate oxide film. The gate electrode 25 is oxidized, and first silicon oxide films 36a, 36b are formed. After the oxide films 36a, 36b have been removed, a second silicon oxide film 28 is deposited, the surface of the gate electrode 25 and the substrate of a heavily doped diffusion layer 31 are exposed by an etching-back operation, and a sidewall 39 is formed. A hollow 37 is reflected on the side face of the sidewall 39, and a hollow 40 is formed. After that, a titanium film 32 which is formed after that becomes discontinuous due to the hollow 40.